

ABSOLUTE MAXIMUM RATINGS
(25°C unless otherwise specified)

Storage Temperature ————— -55°C to +125°C
Operating Temperature ————— -30°C to +100°C
Lead Soldering Temperature
(1/16 inch (1.6mm) from case for 10 secs) 260°C

INPUT DIODE

Forward Current ————— ±50mA
Power Dissipation ————— 70mW

OUTPUT TRANSISTOR

Collector-emitter Voltage BV_{CEO} ——— 80V
Emitter-collector Voltage BV_{ECO} ——— 6V
Collector Current ————— 50mA
Power Dissipation ————— 150mW

POWER DISSIPATION

Total Power Dissipation ————— 200mW
(derate linearly 2.67mW/°C above 25°C)

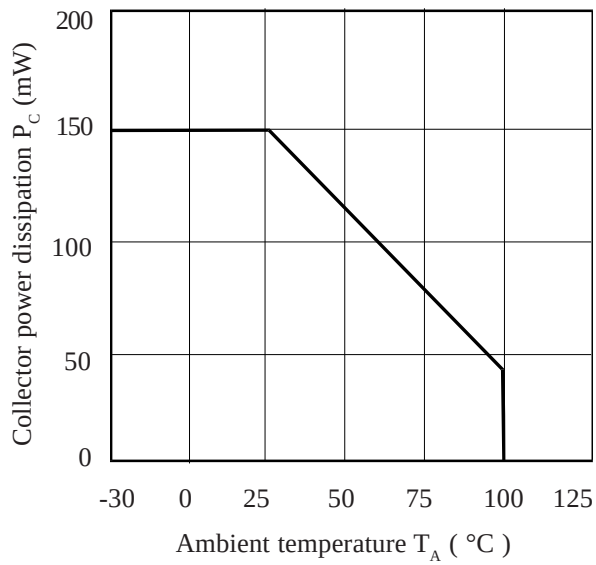
ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ Unless otherwise noted)

PARAMETER		MIN	TYP	MAX	UNITS	TEST CONDITION
Input	Forward Voltage (V_F)		1.2	1.4	V	$I_F = \pm 10\text{mA}$
Output	Collector-emitter Breakdown (BV_{CEO}) (Note 2)	80			V	$I_C = 1\text{mA}$
	Emitter-collector Breakdown (BV_{ECO})	6			V	$I_E = 100\mu\text{A}$
	Collector-emitter Dark Current (I_{CEO})			100	nA	$V_{CE} = 20\text{V}$
Coupled	Current Transfer Ratio (CTR) (Note 2) PS2505-1, PS2505-2, PS2505-4	80		600	%	$\pm 5\text{mA} I_F, 5\text{V } V_{CE}$
	Collector-emitter Saturation Voltage $V_{CE(SAT)}$			0.3	V	$\pm 10\text{mA} I_F, 2\text{mA} I_C$
	Input to Output Isolation Voltage V_{ISO}	5300 7500			V_{RMS} V_{PK}	See note 1 See note 1
	Input-output Isolation Resistance R_{ISO}	5×10^{10}			Ω	$V_{IO} = 500\text{V}$ (note 1)
	Output Rise Time t_r Output Fall Time t_f		4 3		μs μs	$V_{CE} = 2\text{V},$ $I_C = 2\text{mA}, R_L = 100\Omega$

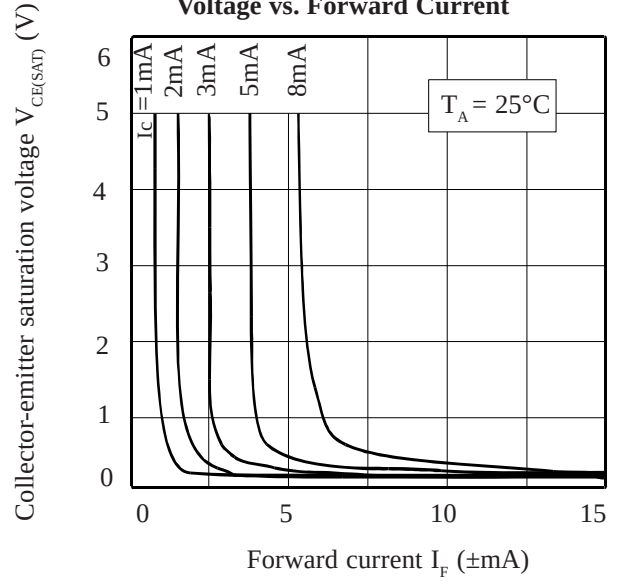
Note 1 Measured with input leads shorted together and output leads shorted together.

Note 2 Special Selections are available on request. Please consult the factory

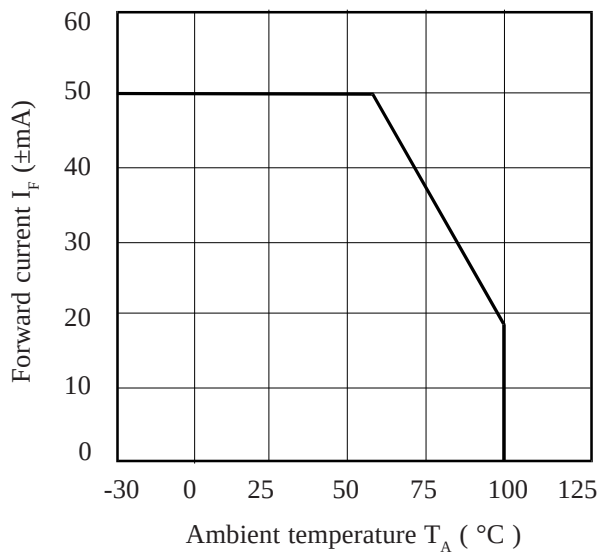
Collector Power Dissipation vs. Ambient Temperature



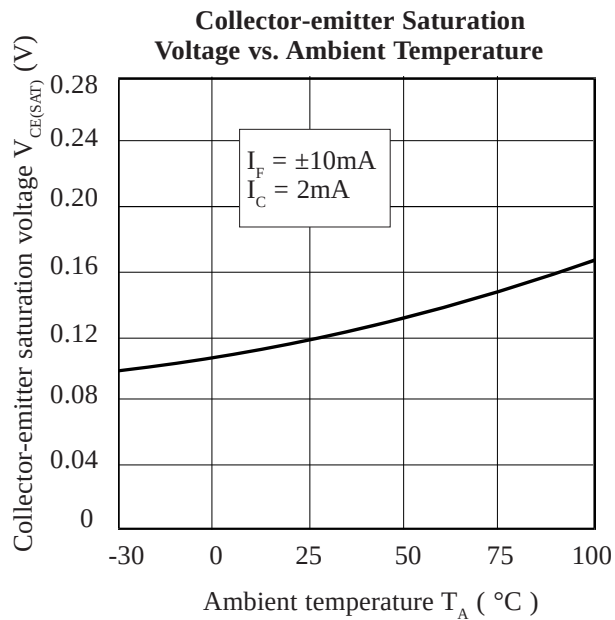
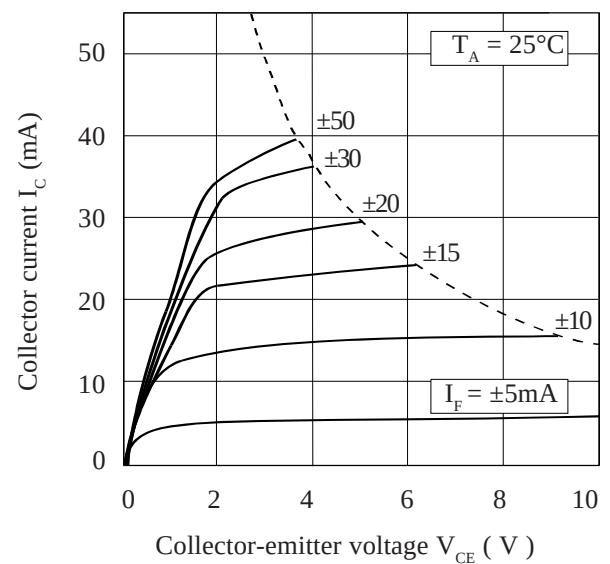
Collector-emitter Saturation Voltage vs. Forward Current



Forward Current vs. Ambient Temperature



Collector Current vs. Collector-emitter Voltage



Current Transfer Ratio vs. Forward Current

